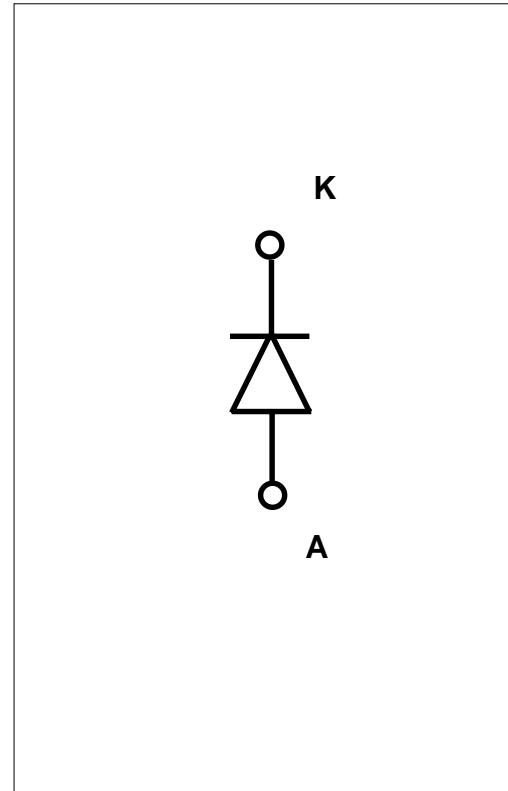
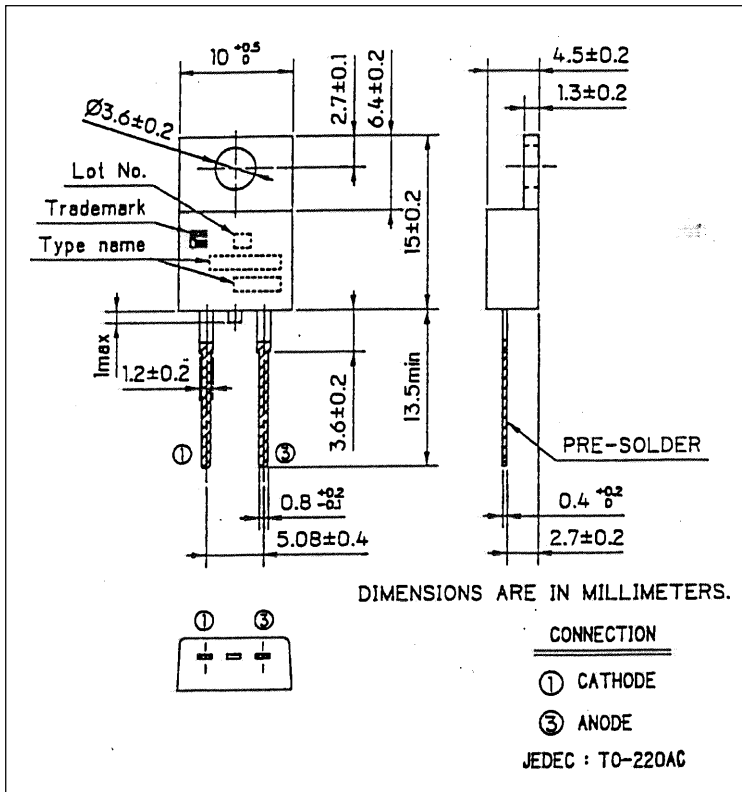


## Fast Recovery Diode for IGBT

### Outline Drawings Units mm

### Equivalent circuit



### Maximum ratings and characteristics

#### Absolute maximum ratings (T<sub>c</sub>=25°C)

Item	Symbol	Test Conditions	Ratings	Units	
Repetitive Reverse Voltage	V <sub>RRM</sub>		1200	V	
Repetitive peak surge current	I <sub>FM</sub>	20kHz Duty 50% Squ. wave	T <sub>c</sub> =123°C	10	A
			T <sub>c</sub> =25°C	32	A
Average rectified forward current	I <sub>F(A)</sub>	DC	10	A	
Non-repetitive peak surge current	I <sub>FSM</sub>	Pulse 10ms, sin. wave	85	A	
Maximum Power Dissipation	P <sub>o</sub>		60	W	
Operating Temperature	T <sub>j</sub>		+150	°C	
Storage Temperature	T <sub>stg</sub>		-40 to +150	°C	
Mounting Screw Torque			50	N-cm	

#### Electrical characteristics (at T<sub>c</sub>=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 1200V	1.0	mA
Forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 10A	3.0	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10A, V <sub>R</sub> =200V, di/dt=100A/μs	0.3	μs

#### Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	R <sub>th(j-c)</sub>	junction to case	2.08	°C/W

Characteristics

